1. General Description

The EM74LVC541A is an 8-bit buffer/line driver with 3-state outputs. The device features two output enables ($\overline{OE}1$ and $\overline{OE}2$). A HIGH on $\overline{OE}n$ causes the associated outputs to assume a high-impedance OFF-state . Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V environments.

Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times.

This device is fully specified for partial power down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

2. Features and Benefits

- Wide supply voltage range from 1.2 V to 5.5 V
- Direct interface with TTL levels
- CMOS low power dissipation
- Overvoltage tolerant inputs to 5.5 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Latch-up performance exceeds 250 mA
- Complies with JEDEC standards:
  - JESD8-7A (1.65 V to 1.95 V)
  - JESD8-5A (2.3 V to 2.7 V)
  - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM ANSI/ESDA/JEDEC JS-001 Class 3A exceeds 6000 V
  - CDM ANSI/ESDA/JEDEC JS-002 Class C3 exceeds 2000 V

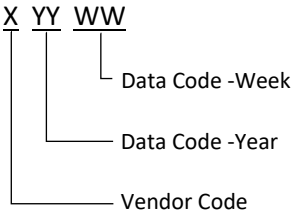
3.Ordering Information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Quantity
EM74LVC541AD	LVC541A XYYWW	SOP-20L	plastic small outline package; 20 leads; body width 7.5 mm	3000
EM74LVC541APW	LVC541A XYYWW	TSSOP-20L	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	3000

MARKING INFORMATION

NOTE: XYYWW = Vendor Code and Data Code.



4.Function Diagram

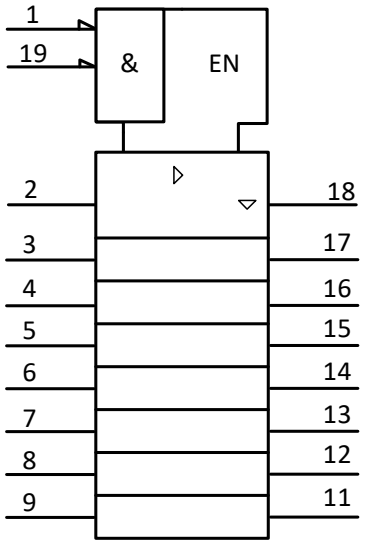


Fig. 1. IEC logic symbol

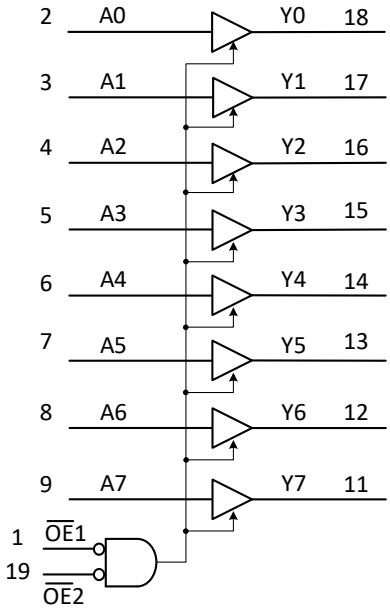


Fig. 2. Functional diagram

5.Pinning Information

5.1. Pinning

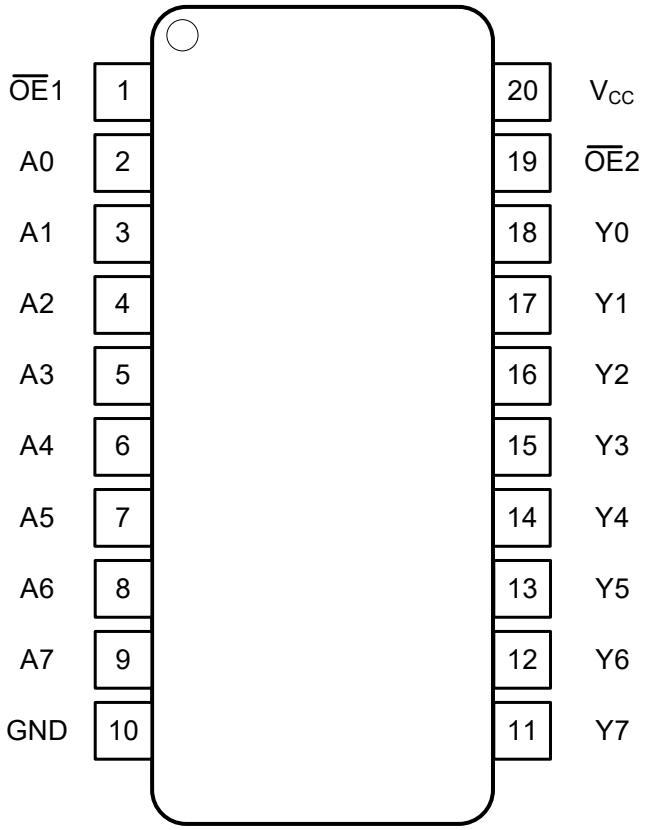


Fig. 3. Top view pin configuration SOP and TSSOP

5.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{OE}1$	1	Output enable input (active LOW)
A0 to A7	2, 3, 4, 5, 6, 7, 8, 9	Data input
GND	10	Ground (0 V)
Y0 to Y7	18, 17, 16, 15, 14, 13, 12, 11	Data output
$\overline{OE}2$	19	Output enable input (active LOW)
V_{CC}	20	Supply voltage

6. Functional Description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

Input			Output
$\overline{OE1}$	$\overline{OE2}$	An	Yn
L	L	L	L
L	L	H	H
X	H	X	Z
H	X	X	Z

7. Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Table 4. Absolute Maximum Ratings

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-50		mA
V_I	Input voltage	[1]	-0.5	6.5	V
I_{OK}	output clamping current	$V_O < 0$ V or $V_O > V_{CC}$		±50	mA
V_O	output voltage	output HIGH or LOW [2]	-0.5	V_{CC}+0.5	V
		output 3-state	-0.5	6.5	V
I_O	output current	V_O = 0 V to V_{CC}		±50	mA
I_{CC}	supply current			100	mA
I_{GND}	ground current		-100		mA
P_{tot}	total power dissipation			500	mW
T_{stg}	storage temperature		-65	150	°C

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

8. Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. EnergyMath does not recommend exceeding them or designing to Absolute Maximum Ratings.

Table 5. Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65		5.5	V
		functional	1.2		5.5	V
V_I	input voltage		0		5.5	V
V_O	output voltage	output HIGH or LOW	0		V_{CC}	V
		output 3-state	0		5.5	V
T_{amb}	ambient temperature		-40		125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.2 V to 2.7 V			20	ns/V
		V_{CC} = 2.7 V to 5.5 V			10	ns/V

9.Static Characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V). Typical values measured at T_{amb} = 25°C (unless otherwise noted).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.2 V	1.08			1.08		V
		V_{CC} = 1.65 V to 1.95 V	0.65V_{CC}			0.65V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7			1.7		V
		V_{CC} = 2.7 V to 3.6 V	2.0			2.0		V
		V_{CC} = 4.5 V to 5.5 V	0.7V_{CC}			0.7V_{CC}		V
V_{IL}	LOW-level input voltage	V_{CC} = 1.2 V			0.12		0.12	V
		V_{CC} = 1.65 V to 1.95 V			0.35V_{CC}		0.35V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V			0.7		0.7	V
		V_{CC} = 2.7 V to 3.6 V			0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V			0.3V_{CC}		0.3V_{CC}	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = -100 µA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1		V
		I_O = -4 mA; V_{CC} = 1.65 V	1.2			1.05		V
		I_O = -8 mA; V_{CC} = 2.3 V	1.9			1.7		V
		I_O = -12 mA; V_{CC} = 2.7 V	2.2			2.1		V
		I_O = -24 mA; V_{CC} = 3.0 V	2.2			2.0		V
		I_O = -32 mA; V_{CC} = 4.5 V	3.8			3.4		V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100 µA; V_{CC} = 1.65 V to 5.5 V			0.1		0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V			0.45		0.65	V
		I_O = 8 mA; V_{CC} = 2.3 V			0.6		0.8	V
		I_O = 12 mA; V_{CC} = 2.7 V			0.4		0.6	V
		I_O = 24 mA; V_{CC} = 3.0 V			0.55		0.8	
		I_O = 32 mA; V_{CC} = 4.5 V			0.55		0.8	V
I_I	input leakage current	V_I = V_{CC} or GND ; V_{CC} = 5.5 V			±2		±10	µA

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; V_{CC} = 5.5 V ; $V_O = V_{CC}$ or GND			±5		±10	µA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V ; V_{CC} =0 V			±10		±20	µA
I_{CC}	supply current	$V_I = V_{IH}$ or GND ; I_O = 0 A ; V_{CC} = 5.5 V			10		20	µA
ΔI_{CC}	additional supply current	per input pin ; $V_I = V_{CC}$ – 0.6V ; I_O = 0 A ; V_{CC} = 2.7 V to 5.5 V			500		5000	µA
C_I	input capacitance			5.0				pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic Characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6. Typical values measured at T_{amb} = 25°C (unless otherwise noted).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	An to Yn; see Fig. 4 [2]						
		V_{CC} = 1.65 V to 1.95 V			35		40	ns
		V_{CC} = 2.3 V to 2.7 V			20		25	ns
		V_{CC} = 3.0 V to 3.6 V			15		20	ns
		V_{CC} = 4.5 V to 5.5 V			10		15	ns
t_{en}	enable time	$\overline{OE}$n to Yn; see Fig. 5 [2]						
		V_{CC} = 1.65 V to 1.95 V			35		40	ns
		V_{CC} = 2.3 V to 2.7 V			20		25	ns
		V_{CC} = 3.0 V to 3.6 V			15		20	ns
		V_{CC} = 4.5 V to 5.5 V			10		15	ns
t_{dis}	disable time	$\overline{OE}$n to Yn; see Fig. 5 [2]						
		V_{CC} = 1.65 V to 1.95 V			35		40	ns
		V_{CC} = 2.3 V to 2.7 V			20		25	ns
		V_{CC} = 3.0 V to 3.6 V			15		20	ns
		V_{CC} = 4.5 V to 5.5 V			10		15	ns
C_{PD}	power dissipation capacitance	Per buffer ; V_{CC} = 3.3 V V_I = GND to V_{CC} [3]		18				pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 3.3 V, and 5 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}. t_{en} is the same as t_{PZL} and t_{PZH}. t_{dis} is the same as t_{PLZ} and t_{PHZ}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz; f_o = output frequency in MHz

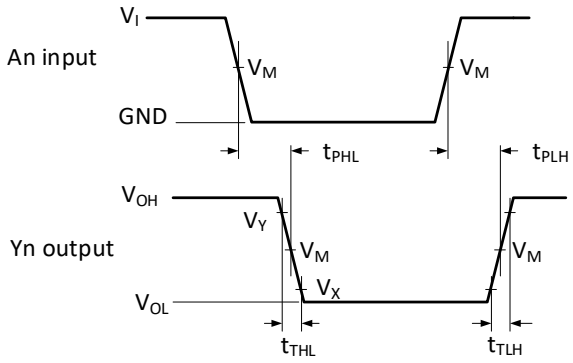
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

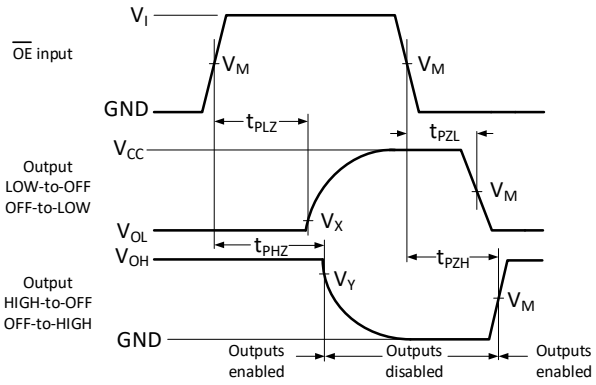
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

10.1. Waveforms and test circuit



Measurement points are given in Table 8.
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig. 4. The input An to output Yn propagation delays

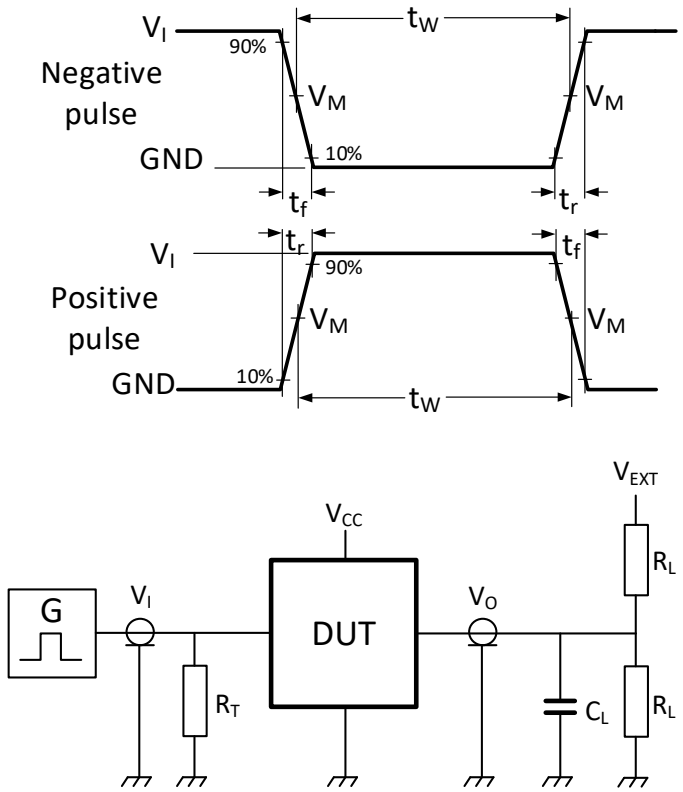


Measurement points are given in Table 8.
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig. 5. 3-state enable and disable times

Table 8. Measurement points

Supply voltage	Input		Output		
V_{CC}	V_I	V_M	V_M	V_X	V_Y
1.65 V to 1.95 V	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.15 V	V_{OH} - 0.15 V
2.3 V to 2.7 V	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.15 V	V_{OH} - 0.15 V
3.0 V to 3.6 V	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} - 0.3 V
4.5 V to 5.5 V	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} - 0.3 V



Test data is given in Table 9.
Definitions for test circuit:
R_L = Load resistance.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
V_{EXT} = External voltage for measuring switching times.

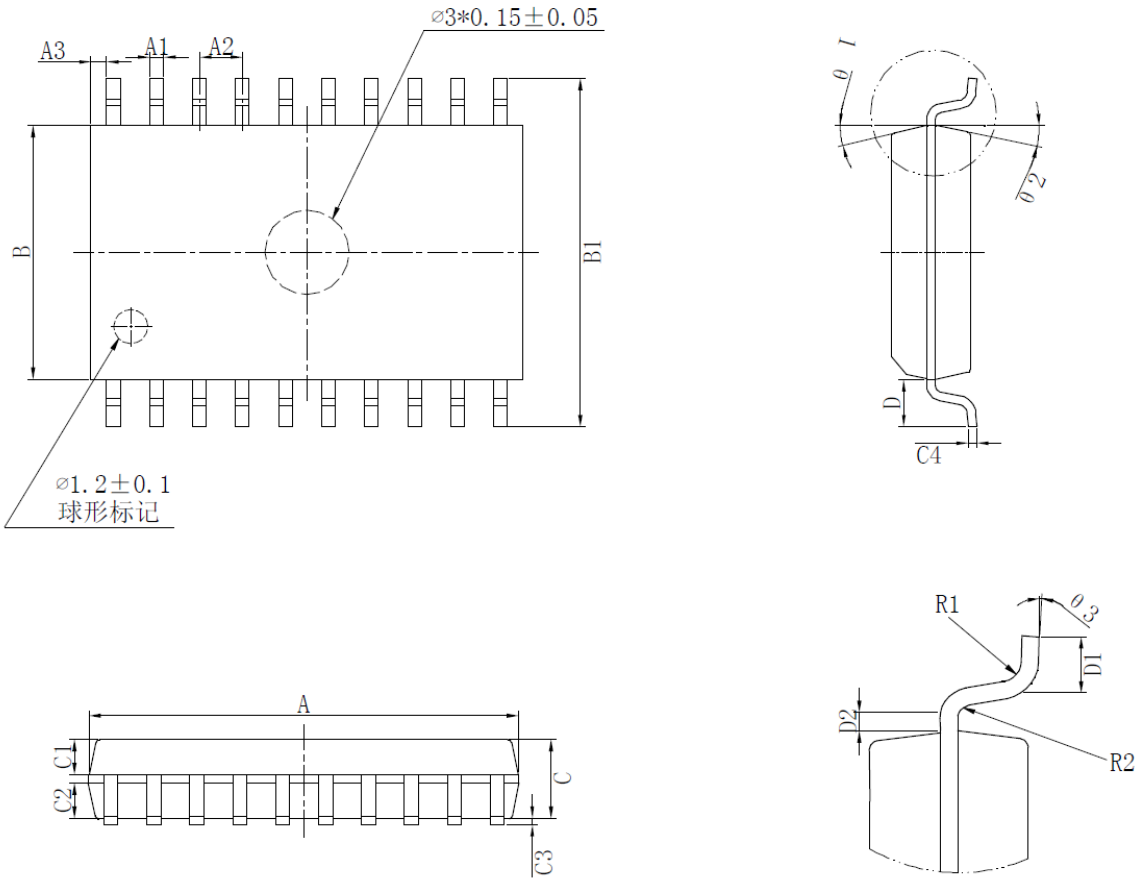
Fig. 6. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		V_{EXT}		
	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65V to 1.95V	V_{CC}	≤ 2 ns	15 pF	2kΩ	open	GND	$2V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2 ns	15 pF	2kΩ	open	GND	$2V_{CC}$
3.0 V to 3.6 V	V_{CC}	≤ 2 ns	15 pF	2kΩ	open	GND	$2V_{CC}$
4.5 V to 5.5 V	V_{CC}	≤ 2 ns	15 pF	2kΩ	open	GND	$2V_{CC}$

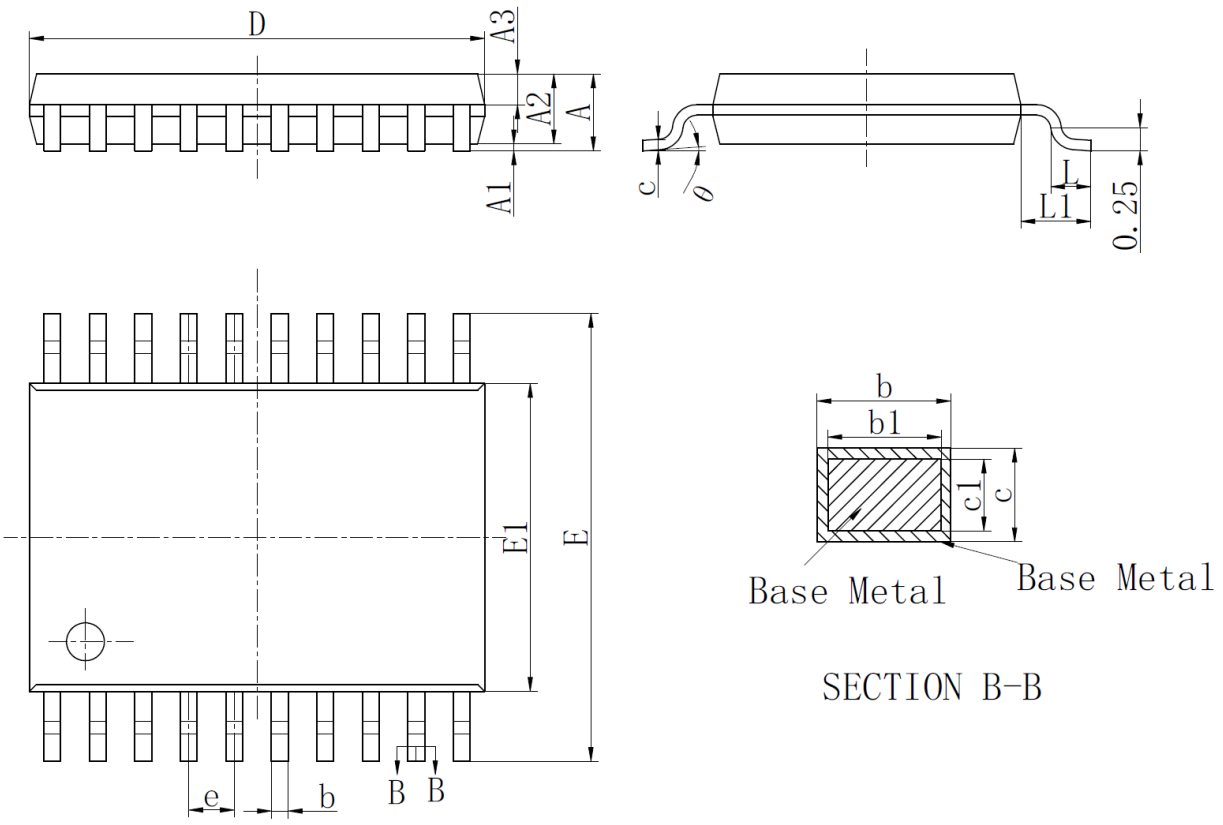
11. Package Outline

SOP-20L



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min.	Max.		Min.	Max.
A	12.600	12.900	C4	0.246	0.262
A1	0.381	0.431	D	1.353	1.453
A2	1.240	1.300	D1	0.764	0.964
A3	0.450	0.460	D2	0.18TYP	
B	7.400	7.600	R1	0.30TYP	
B1	10.206	10.406	R2	0.20TYP	
C	2.150	2.300	θ1	12° TYP	
C1	0.938	1.038	θ2	12° TYP	
C2	0.938	1.2038	θ3	0° ~ 8°	
C3	0.145	0.205			

TSSOP-20L



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min.	Max.		Min.	Max.
A	-	1.20	E	6.20	6.60
A1	0.05	0.15	e	0.65BSC	
A2	0.80	1.05	L	0.45	0.75
A3	0.39	0.49	L1	1.00REF	
b	0.20	0.28	θ	0°	8°
b1	0.19	0.25			
c	0.13	0.17			
c1	0.12	0.14			
D	6.40	6.60			
E1	4.30	4.50			

12. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
CDM	Charged Device Model

13. Revision History

Table 11. Revision history

Document ID	Release Date	Data sheet status	Change notice	Supersedes
EM74LVC_541A Rev. 0.9	Apr 10, 2025	Draft datasheet		